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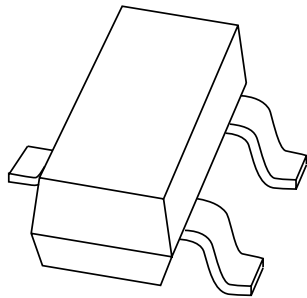
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PMBD6100 High-speed double diode

Product data sheet
Supersedes data of 1999 May 11

2003 Mar 25

High-speed double diode

PMBD6100

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- General application
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching in surface mounted circuits.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBD6100	*5B

Note

1.

* = p : Made in Hong Kong.

* = t : Made in Malaysia.

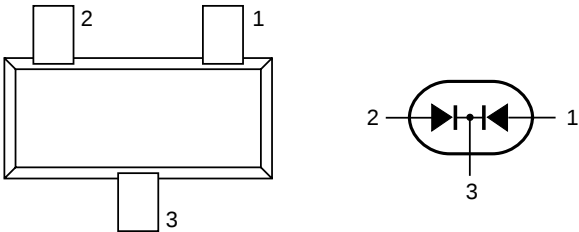
* = W : Made in China.

DESCRIPTION

The PMBD6100 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	anode (a1)
2	anode (a2)
3	common cathode



Top view

MAM108

Fig.1 Simplified outline (SOT23) and symbol.

LIMITING VALUES					
In accordance with the Absolute Maximum Rating System (IEC 60134).					
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V _{RRM}	repetitive peak reverse voltage		–	85	V
V _R	continuous reverse voltage		–	70	V
I _F	continuous forward current	single diode loaded; note 1; see Fig.2	–	215	mA
		double diode loaded; note 1; see Fig.2	–	125	mA

High-speed double diode

PMBD6100

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current		–	450	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\text{ }\mu\text{s}$ $t = 1\text{ ms}$ $t = 1\text{ s}$	– – –	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3 $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 50\text{ mA}$ $I_F = 100\text{ mA}$	550 – – 0.85	700 855 1 1.1	mV mV V V
I_R	reverse current	see Fig.5 $V_R = 50\text{ V}$ $V_R = 50\text{ V}$; $T_j = 150\text{ °C}$	– –	100 50	nA μA
C_d	diode capacitance	$f = 1\text{ MHz}$; $V_R = 0$; see Fig.6	–	1.5	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}$; $t_r = 20\text{ ns}$; see Fig.8	–	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

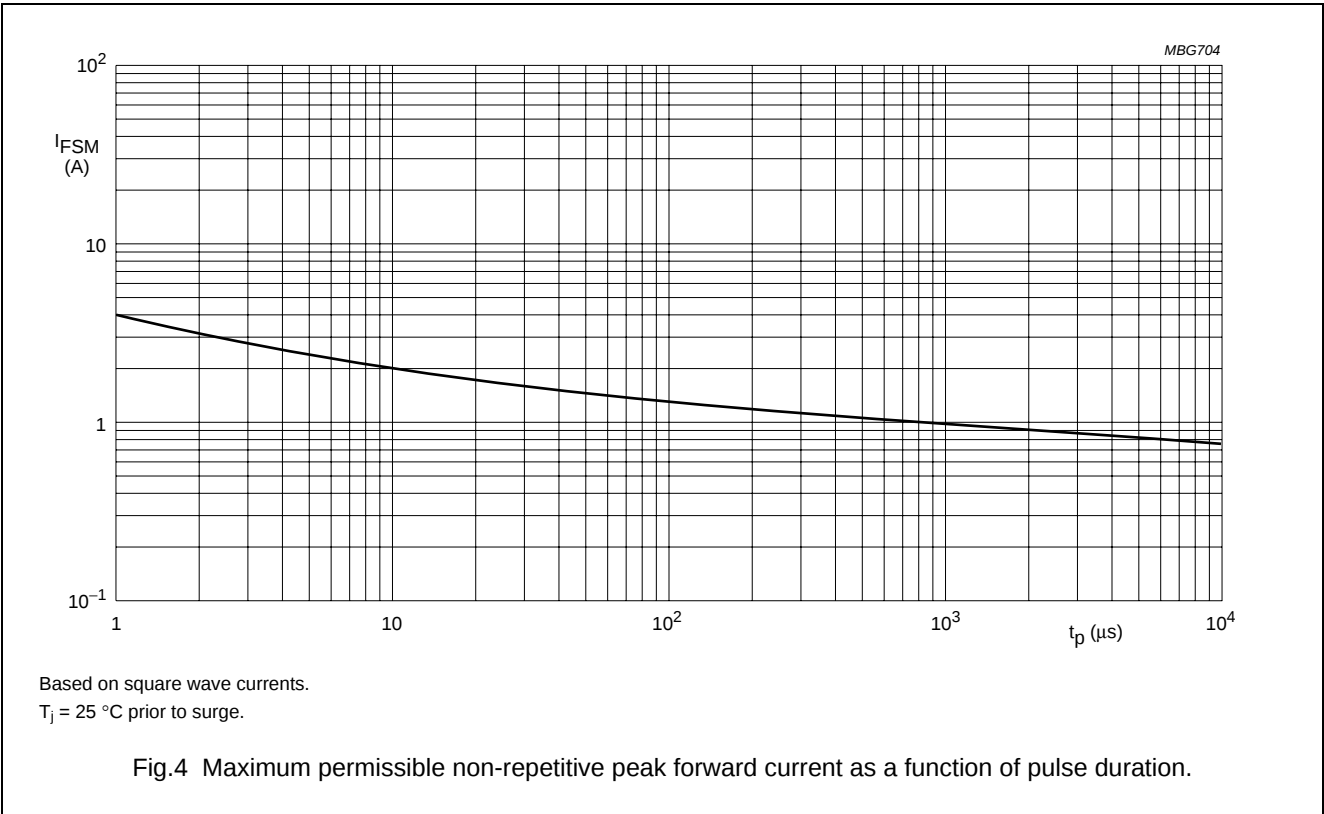
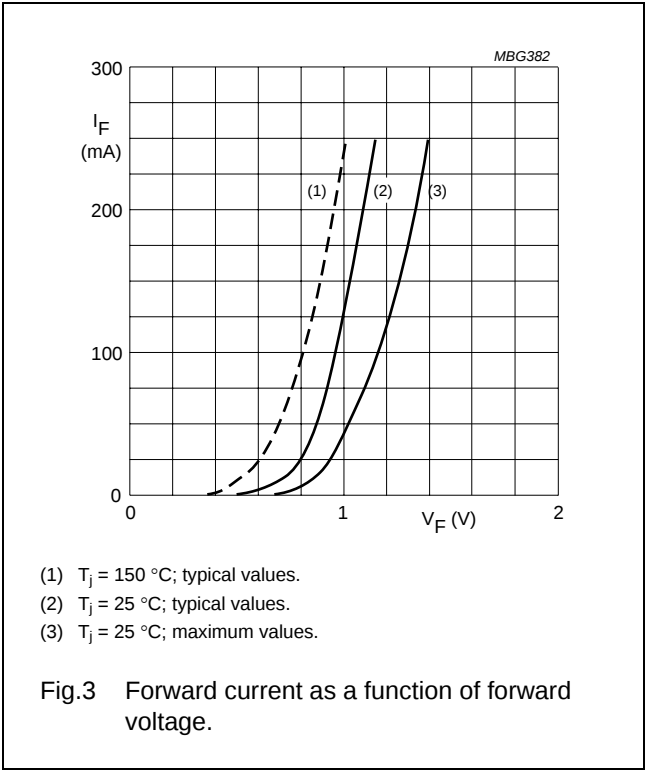
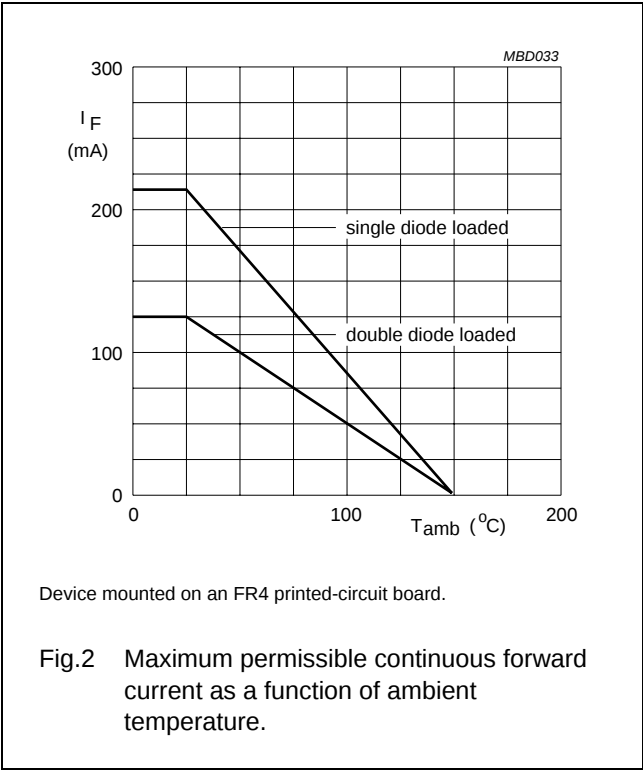
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

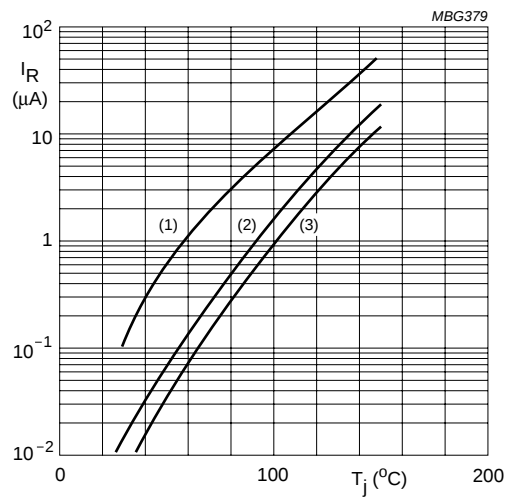
PMBD6100

GRAPHICAL DATA



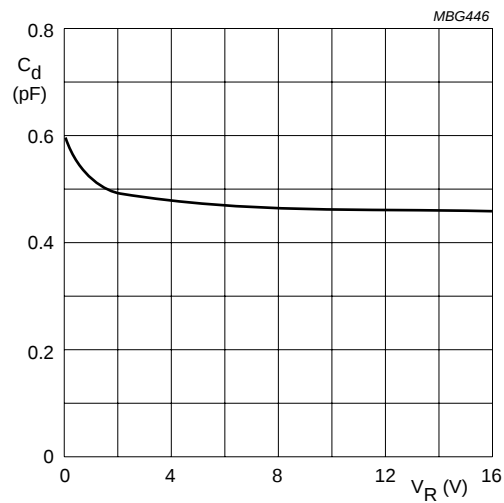
High-speed double diode

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- (1) $V_R = 50$ V; maximum values.
- (2) $V_R = 50$ V; typical values.
- (3) $V_R = 30$ V; typical values.

Fig.5 Reverse current as a function of junction temperature.

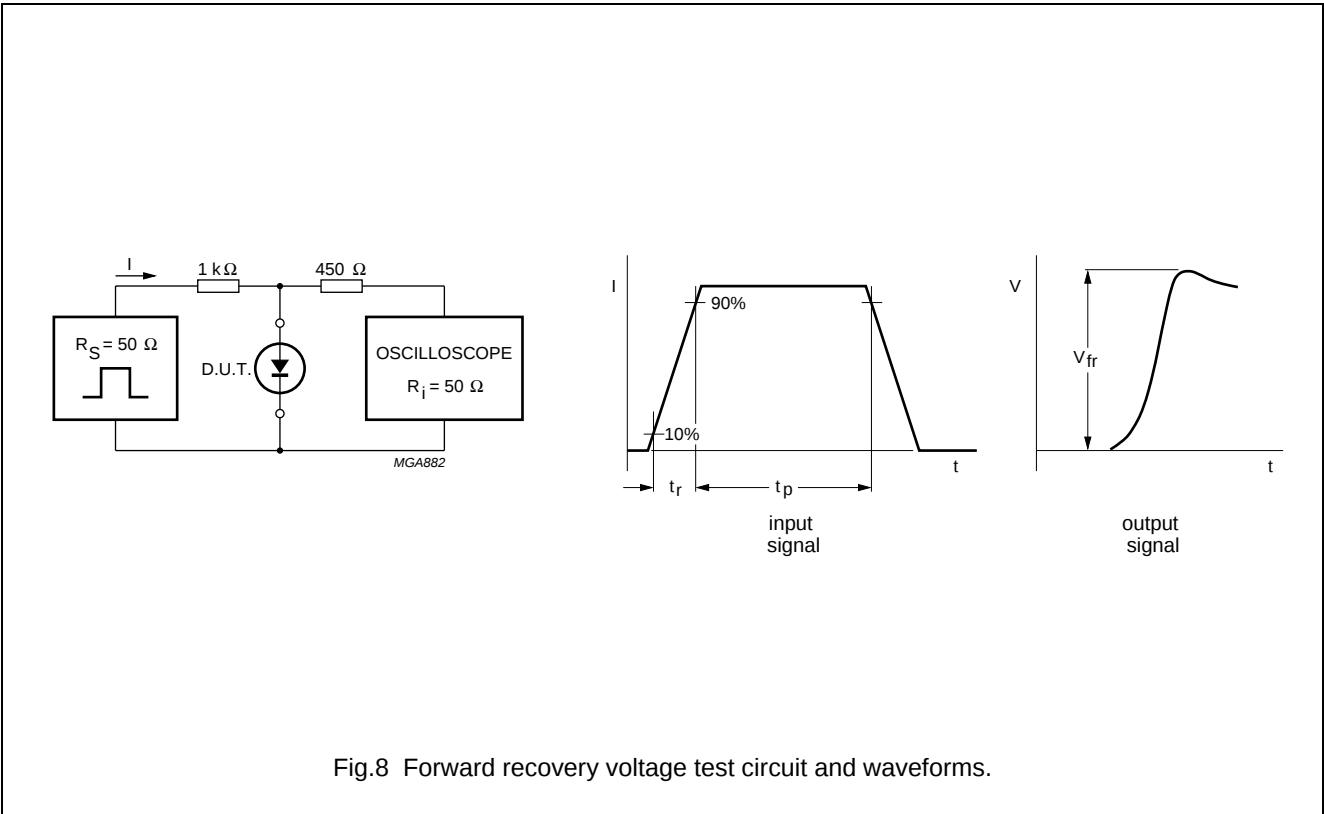
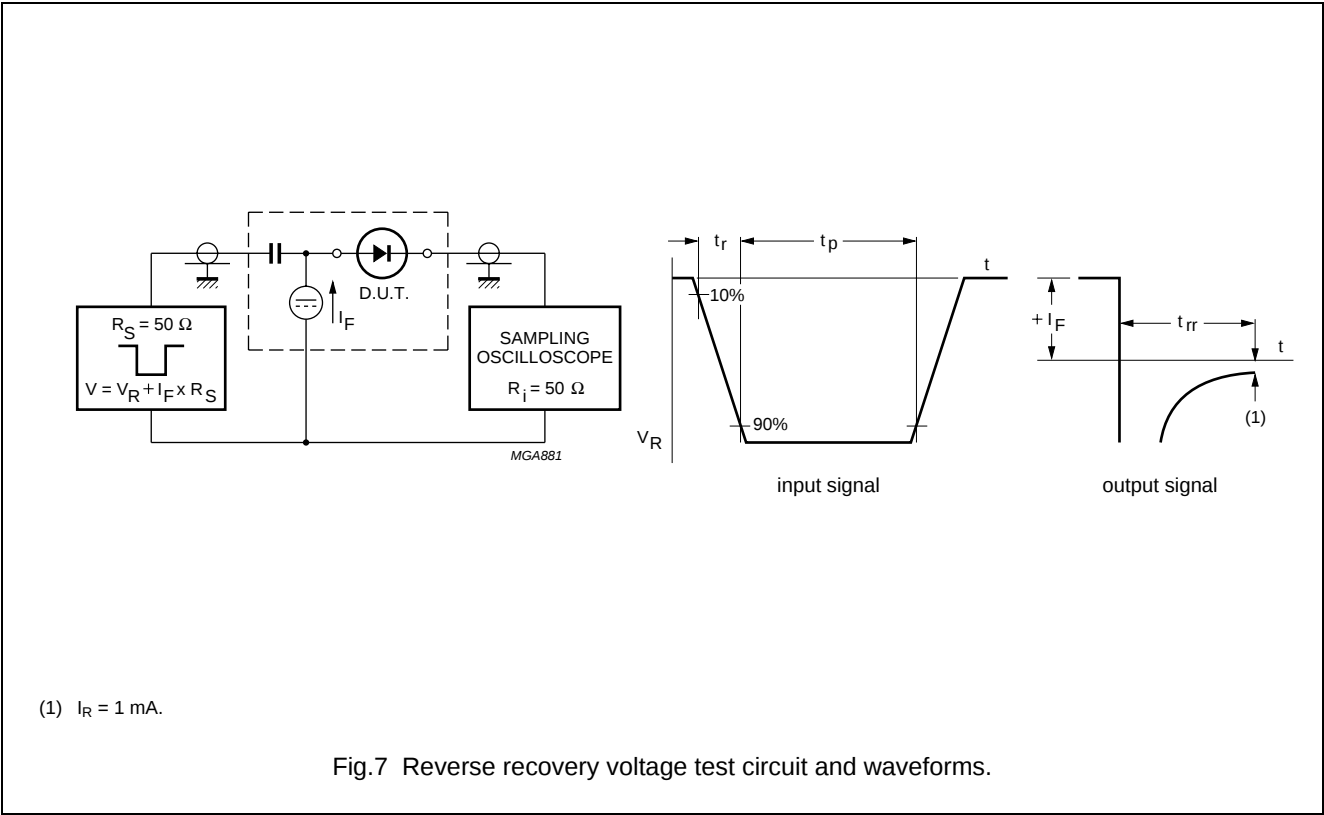


$f = 1$ MHz; $T_j = 25$ $^{\circ}C$.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed double diode

PMBD6100



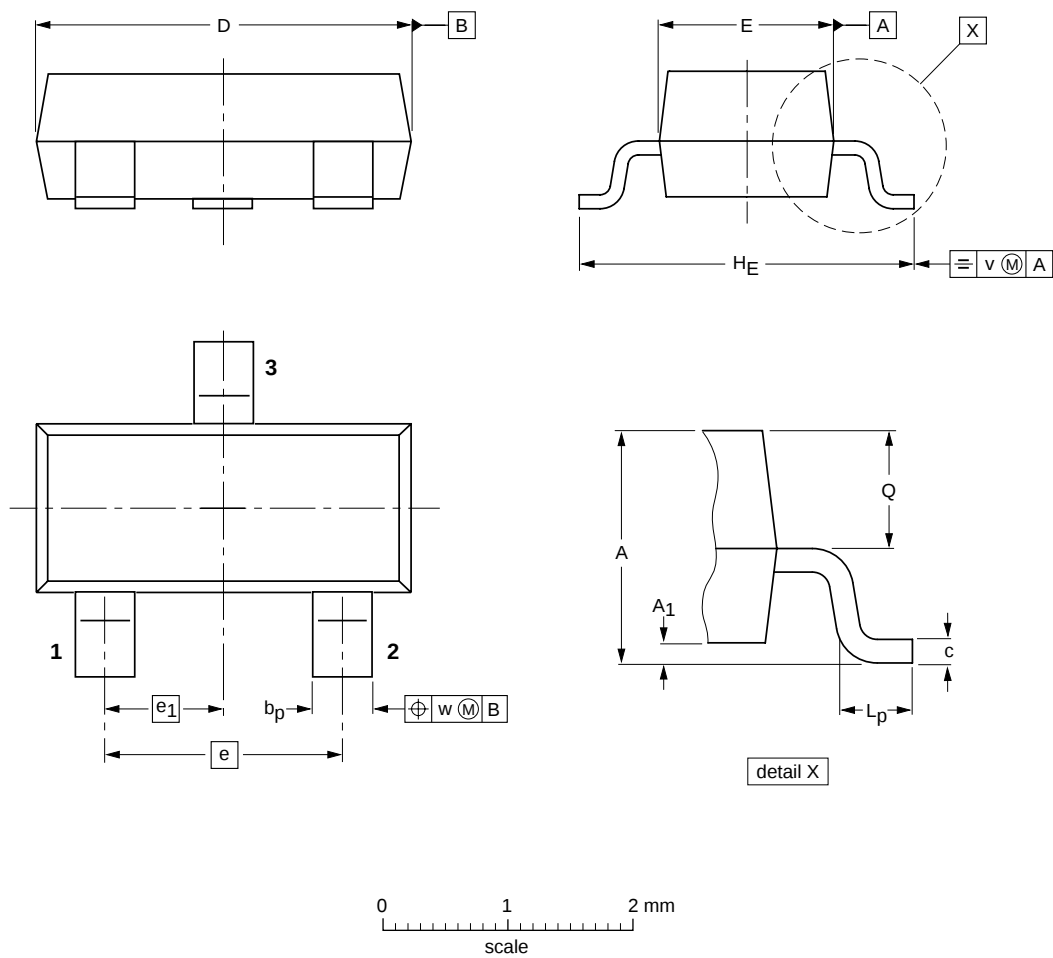
High-speed double diode

PMBD6100

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

High-speed double diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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Contact information

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